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PTO/SB/17 (12-04v2)

Approved for use through 7/31/2006. OMB 0651-0032
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

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Effective on 12/08/2004. Fees pursuant to the Consolidated Appropriations Act, 2005 (H.R. 4818). FEE TRANSMITTAL For FY 2005		Complete if Known	
<input type="checkbox"/> Applicant claims small entity status. See 37 CFR 1.27		Patent Number	6,949,402
TOTAL AMOUNT OF PAYMENT		Issue Date	September 27, 2005
(\$)		First Named Inventor	John T. Moore
100.00		Examiner Name	Craig Thompson
		Art Unit	2813
		Attorney Docket No.	M4065.0694/P694-A

METHOD OF PAYMENT (check all that apply)

<input type="checkbox"/> Check	<input checked="" type="checkbox"/> Credit Card	<input type="checkbox"/> Money Order	<input type="checkbox"/> None	<input type="checkbox"/> Other (please identify):
<input checked="" type="checkbox"/> Deposit Account Deposit Account Number: 04-1073 Deposit Account Name: Dickstein Shapiro Morin & Oshinsky LLP				
For the above-identified deposit account, the Director is hereby authorized to: (check all that apply)				
<input checked="" type="checkbox"/> Charge fee(s) indicated below		<input type="checkbox"/> Charge fee(s) indicated below, except for the filing fee		
<input checked="" type="checkbox"/> Charge any additional fee(s) or underpayment of fee(s) under 37 CFR 1.16 and 1.17		<input checked="" type="checkbox"/> Credit any overpayments		

FEE CALCULATION**1. BASIC FILING, SEARCH, AND EXAMINATION FEES**

Application Type	FILING FEES		SEARCH FEES		EXAMINATION FEES		Fees Paid (\$)
	Fee (\$)	Small Entity Fee (\$)	Fee (\$)	Small Entity Fee (\$)	Fee (\$)	Small Entity Fee (\$)	
Utility	300	150	500	250	200	100	790.00
Design	200	100	100	50	130	65	
Plant	200	100	300	150	160	80	
Reissue	300	150	500	250	600	300	
Provisional	200	100	0	0	0	0	

2. EXCESS CLAIM FEES

Fee Description	Fee (\$)	Small Entity Fee (\$)
Each claim over 20 (including Reissues)	50	25
Each independent claim over 3 (including Reissues)	200	100
Multiple dependent claims	360	180

Total Claims	Extra Claims	Fee (\$)	Fee Paid (\$)	Multiple Dependent Claims
				Fee (\$)
				Fee Paid (\$)
Indep. Claims	Extra Claims	Fee (\$)	Fee Paid (\$)	

3. APPLICATION SIZE FEE

If the specification and drawings exceed 100 sheets of paper (excluding electronically filed sequence or computer listings under 37 CFR 1.52(e)), the application size fee due is \$250 (\$125 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s).

Total Sheets	Extra Sheets	Number of each additional 50 or fraction thereof	Fee (\$)	Fee Paid (\$)

4. OTHER FEE(S)

	Fees Paid (\$)
Non-English Specification, \$130 fee (no small entity discount)	
Other (e.g., late filing surcharge): 1811 Certificate of Correction	100.00

SUBMITTED BY

Signature		Registration No. (Attorney/Agent)	28,371	Telephone	(202) 828-2232
Name (Print/Type)	Thomas J. D'Amico	Date	November 7, 2005		

Certificate
NOV 14 2005
of Correction



Docket No.: M4065.0694/P694-A
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:
John T. Moore, et al.

Examiner: Craig Thompson

Patent No.: 6,949,402

Art Unit: 2813

Issued: September 27, 2005

For: METHOD OF FORMING A NON-
VOLATILE RESISTANCE VARIABLE
DEVICE

REQUEST FOR CERTIFICATE OF CORRECTION
PURSUANT TO 37 C.F.R. §§ 1.322 & 1.323

Commissioner for Patents
Attention: Certificate of Correction Branch
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentees noted typographical errors which should be corrected.

In the Specification:

Patentees made the following typographical error which should be corrected:

Col. 2, line 30, reads "example such" and should read --example of such--.

In the Claims:

Patentees made the following typographical error which should be corrected:

11/08/2005 CNGUYEN 00000082 6949402

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100.00 OP

DSMDB.2002918.1

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Claim 16, col. 7, line 44, reads "portion of said of said" and should read --portion of said--.

In the Foreign Patent Documents portion of References Cited Portion:

The USPTO made the following typographical errors which should be corrected:

"JP 56126915 A 10/1981" should read --JP 56126916 A 10/1981--.

In the Other Publications portion of References Cited Portion:

The USPTO made the following typographical errors which should be corrected:

"Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an uppere bilayer electrode, Thin Solid Films 131 (1985) L61-L64." should read

--Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin Solid Films 131 (1985) L61-L64.--;

"Deamaley, G.; Stoneham, A.M.; Morgan, D.V., Electrical phenomena in amorphous oxide films, Rep. Prog. Phys. 33 (1970) 1129-1191." should read

--Dearnaley, G.; Stoneham, A.M.; Morgan, D.V., Electrical phenomena in amorphous oxide films, Rep. Prog. Phys. 33 (1970) 1129-1191.--;

"El Ghrandi. R.; Calas, J.; Gailbert., G.; Averous, M., Silver photodissolution in amorphous chalcogenide thin films, Thin Solid Films 218 (1992) 259-273." should read

--El Ghrandi. R.; Calas, J.; Galibert., G.; Averous, M., Silver photodissolution in amorphous chalcogenide thin films, Thin Solid Films 218 (1992) 259-273.--;

"Halfz, M.M.; Ibrahim, M.M.; Dongol, M.; Hammad, F.H., Effect of composition on the structure and electrical properties of As-Se-Cu glasses, J. Apply. Phys. 54 (1983) 1950-1954." should read

--Haifz, M.M.; Ibrahim, M.M.; Dongol, M.; Hammad, F.H., Effect of composition on the structure and electrical properties of As-Se-Cu glasses, J. Appl. Phys. 54 (1983) 1950-1954.--;

"Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=Ni, Bi), Mat. Chem. And Phys. 28 (1991) 253-258." should read

--Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=Ni, Bi), Mat. Chem. And Phys. 28 (1991) 253-258.--;

"Lolobov, A.V., "Photodoping of amorphous chalcogenides by metals", Advance in Physics, 1991, vol. 40, No. 5, pp. 625-684." should read

--Kolobov, A.V., "Photodoping of amorphous chalcogenides by metals", Advance in Physics, 1991, vol. 40, No. 5, pp. 625-684.--; and

"Huggett et al., Development of silver sensitized germanium selenide photoresist by reactive sputter etching in SF₆, 42 Appl. Phys. Lett., No. 7, pp. 592-594 (Apr. 1983). " should read

--Huggett et al., Development of silver sensitized germanium selenide photoresist by reactive sputter etching in SF₆, 42 Appl. Phys. Lett., No. 7, pp. 592-594 (Apr. 1983). --.

The typographical error in the specification, Col. 3, line 30, was found in the application as-filed by the Patentees. Similarly, the typographical error in the claims, claim 16, col. 7, line 44, was found in the application as-filed by the Patentees. These typographical errors now sought to be corrected are inadvertent typographical errors, the correction of which does not involve new matter or require reexamination. Please charge our Credit Card in the amount of \$100.00 covering the fee set forth in 37 CFR 1.20(a). Credit Card Payment Form SB-2038, with a signature from an authorized cardholder, is enclosed.

The typographical errors in the References Cited portion were not in the application as-filed or amended by the Patentees. These errors sought to be corrected are inadvertent typographical errors on the part of the USPTO, the correction of which does not involve new matter or require reexamination.

Transmitted herewith is a proposed Certificate of Correction effecting such amendment. Patentees respectfully solicit the granting of the requested Certificate of Correction.

NOV 17 2005

NOV 17 2005

Patent No.: 6,949,402

Docket No.: M4065.0694/P694-A

The Director is also hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0694/P694-A.

Dated: November 7, 2005

Respectfully submitted,

By 

Thomas J. D'Amico

Registration No.: 28,371

James C. Derry

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Attorneys for Patentees

NOV 17 2005

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

Page 1 of 2

PATENT NO. : 6,949,402
APPLICATION NO. : 10/777,755
ISSUE DATE : September 27, 2005
INVENTOR(S) : John T. Moore, et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Specification:

Col. 3, line 30, reads "example such" and should read --example of such--.

In the Claims:

Claim 16, col. 7, line 44 reads "portion of said of said" and should read --portion of said--.

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